

STPS660CB(-TR)

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	2x3 A	
V _{RRM}	60 V	
V _F (max)	0.59 V	

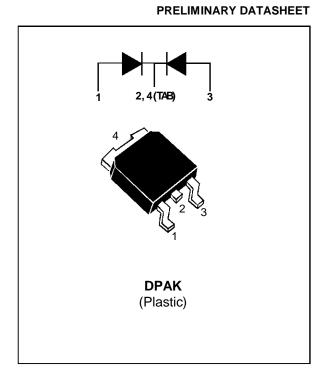
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY
- TAPE AND REEL OPTION: -TR

DESCRIPTION

High voltage dual Schottky rectifier suited to Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage		60	V
I _{F(RMS)}	RMS Forward Current		6	Α
I _{F(AV)}	Average Forward Current	Tcase = 120°C δ = 0.5	3	А
I _{FSM}	Surge Non Repetitive Forward Current	tp = 10 ms Sinusoidal	50	А
I _{RRM}	Repetitive Peak Reverse Current	tp = 2 μs F = 1KHz	1	А
T _{stg}	Storage Temperature Range		- 65 to + 150	°C
Tj	Max. Junction Temperature		125	°C
dV/dt	Critical Rate of Rise of Reverse Voltage		1000	V/μs

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{TH} (j-c)	Junction to Case Thermal Resistance	Per diode	3.5	°C/W
		Total	2	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Тур.	Max.	Unit
I _R *	Reverse leakage Current	Tj = 25°C	V _R = 60 V			30	μΑ
		Tj = 125°C			2.5	10	mA
V _F **	Forward Voltage drop	Tj = 25°C	I _F = 3 A			0.65	V
		Tj = 125°C	I _F = 3 A		0.55	0.59	

Pulse test: * tp = 5 ms, duty cycle < 2 %

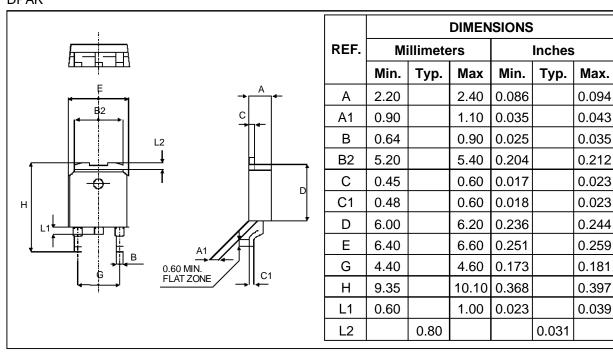
To evaluate the maximum conduction losses use the following equation:

 $P = 0.49 \text{ x } I_{F(AV)} + 0.035 I_{F}^{2}(RMS)$

Typical junction capacitance, $V_R = 0 V$ F = 1 MHz

Hz $T_i = 25^{\circ}C$ C = 815pF

PACKAGE MECHANICAL DATA DPAK



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^{**} tp = 380 μs, duty cycle < 2%